

6/8inch Vertical Furnace

Model: SA-Flouris X201H/P

SA-FLOURIS X201H/P is a vertical batch furnace for 6/8-inch Si, SiC and GaN wafers, covering gate oxide, FOX, BPSG reflow and multi-type annealing processes. It delivers $\pm 1^{\circ}\text{C}$ precise temperature control and ultra-fine film thickness uniformity below 0.6% WIW. Strict metal contamination and particle management enable stable mass production for power, logic and MEMS semiconductor manufacturing.



Feature

- Precision Temperature Control
- Superior uniformity
- Flexible batch capacity options
- Mass Production

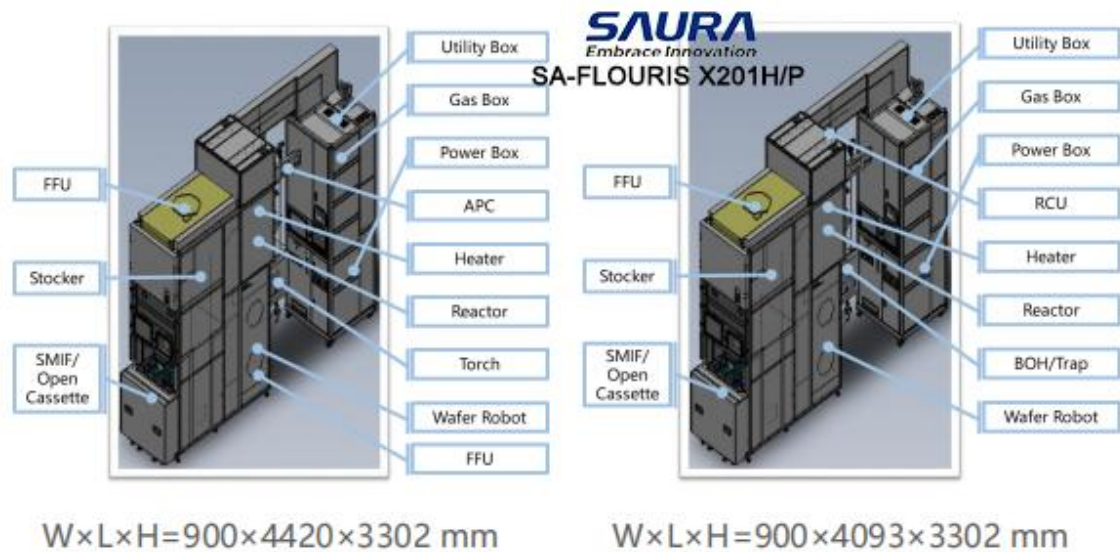
Application

- Logic
- Power
- Si/SiC/GaN
- MEMS

Specifications:

Parameter	Descriptions
Wafer Size	6/8inch
Process	FOX/STI Anneal/Pad-Oxide/Gate Oxide/BPSG Reflow/Final Alloy/Cu Anneal/N ₂ Anneal/Polyimide Cure
Compatible Materials	Si/SiC/GaN
Teamperature Control Accuracy	$\leq \pm 1^{\circ}\text{C}$
Flat Zone Length	860mm
Batch Size	150/125
SMIF/Open Cassette/OHT	Option
N ₂ Load Lock	Option
AGC	Option
Particle Control	$\leq 20@0.16\mu\text{m}$
Uniformity(WIW/WTW/LTL)	$\leq 2\%/1.5\%/1.5\%$
Metal Contamination (ICP-MS/TXRF)	5E10
Loccalization Progress	Continuous improvement
W×L×H	900×4420×3302 mm/900×4093×3302 mm

Package:

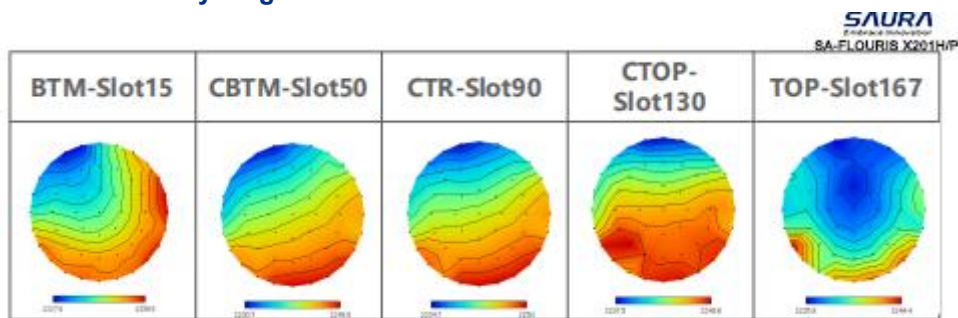


Performance:

Thickness uniformity results(49Point,EE3mm)

Monitor Position		Slot15	Slot50	Slot90	Slot130	Slot167
Average	[Å]	2261.9	2256.9	2259.5	2262.7	2260.1
Range	[Å]	26.19	15.23	12.50	7.85	4.01
Stdev.	[Å]	8.95	4.67	4.14	2.78	1.43
WIW Unif	[±%]	0.58	0.34	0.28	0.17	0.09
WTW Unif	[±%]	0.13				

Thickness uniformity diagram



Total

